

L Number	Hits	Search Text	DB	Time stamp
1	57	chalcogenide adj glass and (non-volatile nonvolatile) near2 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/12 14:23
2	45	chalcogenide adj glass and (non-volatile nonvolatile) near2 memory and method.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/12 14:25
3	6	chalcogenide adj glass.ti,ab,clm. and (non-volatile nonvolatile) near2 memory.ti,ab,clm. and method.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/12 14:27
4	3715	((257/296) or (257/297) or (257/298) or (257/299) or (257/300) or (257/63) or (257/52) or (257/55) or (257/2) or (501/11) or (501/19) or (501/42)).CCLS.	USPAT; US-PGPUB	2004/06/12 14:29
5	8	((257/296) or (257/297) or (257/298) or (257/299) or (257/300) or (257/63) or (257/52) or (257/55) or (257/2) or (501/11) or (501/19) or (501/42)).CCLS.) and germanium and selenide and (silver ag) and (non-volatile nonvolatile) near2 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/12 14:29
-	0	("chalcogenide adj glass.clm. and chalcogenide.ti.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 14:58
-	24	chalcogenide adj glass.clm. and chalcogenide.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:05
-	3	pcram.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:06
-	0	pcram.ti,ab,clm. and processor.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:07
-	1285	ram near3 processor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:07
-	209	ram near3 processor.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:07
-	5	ram near3 processor.ti. and processor.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:24
-	36	chalcogenide near4 use	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:26

-	0	chalcogenide near6 (dop\$3 or impurit\$3) near6 (metal or silver or ag or copper or cu or platinum or pt or gold or au or cadmium or cd or ruthenium or ru or cobalt or co or zinc or zn or chromium or cr or manganese or mn or nickel or ni) and memory adj2 (cell or device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 14:29
-	0	chalcogenide adj glass near12 (metal or silver or ag or copper or cu or platinum or pt or gold or au or cadmium or cd or ruthenium or ru or cobalt or co or zinc or zn or chromium or cr or manganese or mn or nickel or ni) and memory adj2 (cell or device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/16 15:51
-	0	chalcogenide adj glass and (metal or silver or ag or copper or cu or platinum or pt or gold or au or cadmium or cd or ruthenium or ru or cobalt or co or zinc or zn or chromium or cr or manganese or mn or nickel or ni) and memory adj2 (cell or device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/16 15:51
-	3	chalcogenide adj glass near12 (metal or silver or ag or copper or cu or platinum or pt or gold or au or cadmium or cd or ruthenium or ru or cobalt or co or zinc or zn or chromium or cr or manganese or mn or nickel or ni) and memory adj2 (cell or device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/16 16:33
-	21	chalcogenide adj glass near12 (metal or silver or ag or copper or cu or platinum or pt or gold or au or cadmium or cd or ruthenium or ru or cobalt or co or zinc or zn or chromium or cr or manganese or mn or nickel or ni) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/16 16:36
-	115	(365/153).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:34
-	6	((365/153).CCLS.) and chalcogenide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:51
-	2	ag adj content and chalcogenide and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:03
-	0	ag adj content and "ag-ge-te" and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:06
-	45	chalcogenide adj glass and (silver or ag) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:07
-	3	chalcogenide adj glass and (silver or ag) near4 (content or concentration) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:39
-	7	(US-3810128-\$ or US-5479382-\$ or US-6084796-\$ or US-6487106-\$ or US-3827033-\$ or US-3721838-\$).did. or (US-20020168820-\$).did.	USPAT; US-PGPUB	2002/12/17 16:41
-	0	"ge se.sub.3" and (silver or ag) near6 (percentage or concentration or content)	USPAT; US-PGPUB	2002/12/17 16:43
-	0	"ge se.sub.3" and (silver or ag) near6 (percentage or concentration or content)	USPAT; US-PGPUB	2002/12/17 16:44

-	0	"ge se.sub."\$1 and (silver or ag) near6 (percentage or concentration or content)	EPO; JPO; DERWENT; IBM TDB	2002/12/17 16:50
-	1	("6487106").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/18 16:09
-	2	(percent or percentage) near4 (silver or ag) and chalcogenide adj glass and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/18 17:48
-	119	(tie adj line or tie-line) and phase adj diagram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 10:35
-	9	(tie adj line or tie-line).ti,ab. and phase adj diagram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 11:07
-	0	("kozicki.in.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 11:07
-	39	kozicki.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 11:12
-	5	((("5761115") or ("5896312") or ("5914893") or ("6084796"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 11:15
-	1	("6469364").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 11:15
-	18	(US-6084796-\$ or US-6487106-\$ or US-3721838-\$ or US-3810128-\$ or US-3827033-\$ or US-6418049-\$ or US-5479382-\$ or US-6469364-\$ or US-6388324-\$ or US-5914893-\$ or US-5896312-\$ or US-5761115-\$ or US-5500532-\$ or US-5314772-\$).did. or (US-20020000666-\$ or US-20020190350-\$ or US-20020168820-\$).did. or (US-5761115-\$).did.	USPAT; US-PGPUB; DERWENT	2002/12/19 11:16
-	2	("6348365").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 12:02
-	2	("6418049").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 12:02
-	0	switching adj field and chalcogenide adj glass and memory and ("Ag-Ge-Se" or (silver or ag) near3 (percent or percentage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 14:31

-	7	switching adj field and chalcogenide adj glass and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 15:38
-	4	switching adj speed and chalcogenide adj glass and memory and (silver or ag)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 15:41
-	36	switching and chalcogenide adj glass and memory and (silver or ag)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 16:59
-	16042	non-volatile adj memory.ti,ab.,clm. and (germanium adj selenide or "ge.sub.x se.sub.1-x" or "Ag-Ge-Se" or (silver or ag) near6 chalcogenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 17:02
-	16042	non-volatile adj memory.ti,ab.,clm. and (germanium adj selenide or "ge.sub.x se.sub.1-x" or "Ag-Ge-Se" or ((silver or ag) near6 chalcogenide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 17:06
-	16042	non-volatile adj memory.ti,ab.,clm. and (germanium adj selenide or "ge.sub.x se.sub.1-x" or "Ag-Ge-Se" or (silver or ag) near6 chalcogenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 17:07
-	1	non-volatile adj memory.ti,ab.,clm. and (germanium adj selenide or "ge.sub.x se.sub.1-x" or "Ag-Ge-Se" or (silver or ag) near6 chalcogenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 18:22
-	231	(dendrite or dendritic) near12 voltage or electric adj field near12 chalcogenide adj glass	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 18:24
-	157	(dendrite or dendritic) near6 voltage or electric adj field near6 chalcogenide adj glass	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 18:24
-	0	(dendrite or dendritic) near6 (voltage or electric adj field) near6 chalcogenide adj glass	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 18:25
-	0	(dendrite or dendritic) near12 (voltage or electric adj field) near12 chalcogenide adj glass	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 18:25
-	3	(dendrite or dendritic) near12 (voltage or electric adj field) and chalcogenide adj glass.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 18:33
-	0	("t.sub.g" ot transition adj temperature) near12 chalcogenide adj glass and photodiffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 18:35
-	0	("t.sub.g" or transition adj temperature) near12 chalcogenide adj glass and photodiffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 18:36

-	0	("t.sub.g" or temperature) near12 chalcogenide adj glass and photodiffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 18:36
-	50	("t.sub.g" or temperature) near12 chalcogenide adj glass	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 18:41
-	0	photodissolution near12 chalcogenide near12 silver	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 18:42
-	3	photodissolution near12 silver	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 18:42
-	0	microelectronic adj programmable adj device and processor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 15:39
-	3	pcram and processor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 16:27
-	799	campbell.in. and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 16:27
-	7	PCRAM.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 16:42
-	4867	(programmable adj2 device or PCRAM).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 16:43
-	214	(programmable adj memory adj device or PCRAM).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 16:44
-	0	(programmable adj memory adj device or PCRAM).ti,ab. and chalcogenide adj glass	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 18:18
-	0	kristy.in. and campbell.in. and chalcogenide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 18:19
-	0	kristy.in. and campbell.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 18:19
-	1	campbell.in. and chalcogenide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 18:20

-	1	("ge.sub.x se.sub.1-x" or "ge.sub.y. se.sub.1-y" or "ag-ge-se") and glass and (silver or ag) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 18:28
-	2	("ge.sub.x se.sub.1-x" or "ge.sub.y. se.sub.1-y" or "ag-ge-se" or "ge.sub.3 se.sub.7") and glass and (silver or ag) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 18:52
-	4	("ge.sub.x se.sub.1-x" or "ge.sub.y. se.sub.1-y" or "ag-ge-se" or "ge.sub."?"se.sub."?) and glass and (silver or ag) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 18:57
-	2	("5761115").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 20:47
-	27	chalcogenide adj glass near5 oxide.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 20:48
-	0	chalcogenide adj glass near5 oxide.ti,ab,clm. and memory.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 20:49
-	0	chalcogenide adj glass near5 oxide.ti,ab,clm. and storage.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/20 20:49
-	692	((257/2) or (257/52) or (257/55) or (257/63) or (257/298)).CCLS.	USPAT; US-PGPUB	2002/12/21 11:59
-	11	((257/2) or (257/52) or (257/55) or (257/63) or (257/298)).CCLS.) and chalcogenide adj glass and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/21 12:00
-	5	((257/2) or (257/52) or (257/55) or (257/63) or (257/298)).CCLS.) and chalcogenide adj glass and memory.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/21 12:01
-	95	(365/163).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/21 12:01
-	57	((365/163).CCLS.) and chalcogenide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/21 12:01
-	59	((257/2) or (257/52) or (257/55) or (257/63) or (257/298)).CCLS.) and chalcogenide adj glass and memory.ti,ab,clm.) or ((365/163).CCLS.) and chalcogenide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/21 12:03
-	5	((257/2) or (257/52) or (257/55) or (257/63) or (257/298)).CCLS.) and chalcogenide adj glass and memory.ti,ab,clm.) or ((365/163).CCLS.) and chalcogenide)) and silver	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/21 12:04

-	31	(US-5596522-\$ or US-5341328-\$ or US-5166758-\$ or US-6487113-\$ or US-6462984-\$ or US-5072423-\$ or US-5272667-\$ or US-5363329-\$ or US-5406509-\$ or US-5314772-\$ or US-6487106-\$ or US-6469364-\$ or US-3721838-\$ or US-3810128-\$ or US-3827033-\$ or US-6348365-\$ or US-6084796-\$ or US-5914893-\$ or US-5896312-\$ or US-5479382-\$ or US-6418049-\$ or US-5761115-\$ or US-6388324-\$ or US-5500532-\$).did. or (US-20020000666-\$ or US-20020190350-\$ or US-20020168820-\$).did. or (JP-03044703-\$).did. or (US-5761115-\$ or US-6348365-\$ or EP-846353-\$).did.	USPAT; US-PGPUB; JPO; DERWENT	2002/12/21 12:59
-	13	chalcogenide adj glass and "ge.sub."?"?"Se.sub."\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/23 11:29
-	193	501/11	USPAT	2003/11/23 15:40
-	199	501/11	USPAT; US-PGPUB	2003/11/23 15:40
-	279	501/19	USPAT; US-PGPUB	2003/11/23 15:40
-	192	501/42	USPAT; US-PGPUB	2003/11/23 15:40
-	0	501/11 and 501/19 and 501/42	USPAT; US-PGPUB	2003/11/23 15:40
-	3	501/19 and 501/42	USPAT; US-PGPUB	2003/11/23 15:57
-	8	germanium and selenium and chalcogenide and silver and phase adj transition	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/23 16:42
-	1	JP-03044703\$-\$DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/23 16:57
-	14	((("6388324") or ("20020000666") or ("5500532") or ("6418049") or ("5751012") or ("5789277") or ("6348365") or ("20020168820") or ("6469364") or ("6348365") or ("6418049") or ("5761115") or ("5896312") or ("5914893") or ("6084796") or ("6635914"))).PN.	USPAT; US-PGPUB	2004/06/11 13:24
-	3	((("6388324") or ("20020000666") or ("5500532") or ("6418049") or ("5751012") or ("5789277") or ("6348365") or ("20020168820") or ("6469364") or ("6348365") or ("6418049") or ("5761115") or ("5896312") or ("5914893") or ("6084796") or ("6635914"))).PN.) and \$6"Ge.sub."\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 18:35
-	2	((("6388324") or ("20020000666") or ("5500532") or ("6418049") or ("5751012") or ("5789277") or ("6348365") or ("20020168820") or ("6469364") or ("6348365") or ("6418049") or ("5761115") or ("5896312") or ("5914893") or ("6084796") or ("6635914"))).PN.) and \$6"Ge.sub."\$6 near6 (glass amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 18:35
-	2	("6487106").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 10:31

-	2	("5761115").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 11:22
-	13	chalcogenide adj glass and "Ge.sub."\$6 and memory adj cell and (non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 11:34
-	13	chalcogenide adj glass and "Ge.sub."\$6 and memory adj cell and (non-volatile nonvolatile) and (silver Ag)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 11:35
-	13	chalcogenide adj glass and "Ge.sub."\$6 and memory adj cell and (non-volatile nonvolatile) and (silver Ag) and (semiconductor semiconducting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 11:40
-	24	(semiconductor semiconducting) near4 (glass glasses) and "Ge.sub."\$9 and (non-volatile non-volatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 11:41
-	20	(semiconductor semiconducting) near2 (glass glasses) and "Ge.sub."\$9 and (non-volatile non-volatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 11:42
-	20	(semiconductor semiconducting) near2 (glass glasses) and "Ge.sub."\$9 and (non-volatile non-volatile) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 11:42
-	8	(semiconductor semiconducting) near2 (glass glasses) and "Ge.sub."\$9 and (non-volatile non-volatile) and memory and \$6"Se.sub."\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 11:42
-	14	(US-5914893-\$ or US-5896312-\$ or US-5789277-\$ or US-6635914-\$ or US-5500532-\$ or US-6469364-\$ or US-5751012-\$ or US-5761115-\$ or US-6388324-\$ or US-6418049-\$ or US-6348365-\$ or US-6084796-\$).did. or (US-20020000666-\$ or US-20020168820-\$).did.	USPAT; US-PGPUB	2004/06/11 13:25
-	0	wo-0221542\$-\$-did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 13:25
-	1	wo-200221542\$-\$-did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 13:26
-	1	wo-200048196\$-\$-did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 13:27
-	0	wo-199748032\$-\$-did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 13:27

-	1	wo-9748032\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 13:28
-	2	wo-9928914\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 13:28
-	0	"Ge.sub.x Se.sub.1-x"\$6 and silver and chalcogenide adj glass and (semiconductor semiconducting) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 15:00
-	27	"Ge.sub.x"\$8 and silver and chalcogenide adj glass and (semiconductor semiconducting) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 18:36
-	18	kozicki.in. and "0.5"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 18:36
-	11	kozicki.in. and "0.5" and "0.1"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 18:40
-	9	kozicki.in. and "0.5" same "0.1"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/12 12:28
-	9	(mitkova.in. kozicki.in.) and "0.5" same "0.1"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 19:28
-	20	(mitkova.in. kozicki.in.) and ("0.4" "0.5" "0.6")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 19:29
-	9	(mitkova.in. kozicki.in.) and ("0.4" "0.5" "0.6") same x	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 19:29
-	1	jp-03044703\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/12 12:30
-	818	integrated adj circuit and processor and memory adj cell and ("same chip" "single chip")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/12 12:31
-	53	integrated adj circuit same processor same memory adj cell and ("same chip" "single chip")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/12 13:04
-	18	integrated adj circuit same processor same memory adj cell same ("same chip" "single chip")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/12 13:11

-	0	integrated adj circuit same processor same memory adj cell same ("same chip" "single chip") same (non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/12 13:11
-	0	(IC integrated adj circuit) same processor same memory adj cell same ("same chip" "single chip") same (non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/12 14:22